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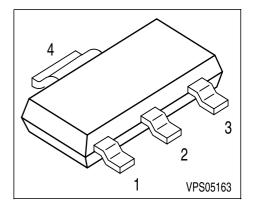
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**PZTA92** 

### PNP Silicon High Voltage Transistor

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: PZTA42 (NPN)



Туре	Marking	Pin Configuration				Package
PZTA92	PZTA 92	1=B	2=C	3=E	4=C	SOT223

# Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V <sub>CEO</sub>	300	V	
Collector-base voltage	V <sub>CBO</sub>	300		
Emitter-base voltage	V <sub>EBO</sub>	5		
DC collector current	I <sub>C</sub>	500	mA	
Base current	I <sub>B</sub>	100		
Total power dissipation, $T_{\rm S}$ = 124 °C	P <sub>tot</sub>	1.5	W	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-65 150		

#### **Thermal Resistance**

Junction - soldering point <sup>1)</sup>	R <sub>thJS</sub>	≤17	K/W

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance



# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.	1	
DC Characteristics						
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	300	-	-	V	
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0						
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	300	-	-		
<i>I</i> <sub>C</sub> = 100 μA, <i>I</i> <sub>E</sub> = 0						
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	5	-	-		
<i>I</i> <sub>E</sub> = 10 μA, <i>I</i> <sub>C</sub> = 0						
Collector cutoff current	I <sub>CBO</sub>	-	-	250	nA	
$V_{\rm CB} = 200 \text{ V}, I_{\rm E} = 0$						
Collector cutoff current	I <sub>CBO</sub>	-	-	20	μA	
$V_{\text{CB}}$ = 200 V, $I_{\text{E}}$ = 0 , $T_{\text{A}}$ = 150 °C						
Emitter cutoff current	I <sub>EBO</sub>	-	-	100	nA	
$V_{\rm EB}$ = 3 V, $I_{\rm C}$ = 0						
DC current gain 1)	h <sub>FE</sub>				-	
<i>I</i> <sub>C</sub> = 1 mA, <i>V</i> <sub>CE</sub> = 10 V		25	-	-		
<i>I</i> <sub>C</sub> = 10 mA, <i>V</i> <sub>CE</sub> = 10 V		40	-	-		
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 10 V		25	-	-		
Collector-emitter saturation voltage1)	V <sub>CEsat</sub>	-	-	0.5	V	
<i>I</i> <sub>C</sub> = 20 mA, <i>I</i> <sub>B</sub> = 2 mA						
Base-emitter saturation voltage 1)	V <sub>BEsat</sub>	-	-	0.9	1	
<i>I</i> <sub>C</sub> = 20 mA, <i>I</i> <sub>B</sub> = 2 mA						

#### **AC Characteristics**

Transition frequency	f <sub>T</sub>	-	100	-	MHz
<i>I</i> <sub>C</sub> = 20 mA, <i>V</i> <sub>CE</sub> = 10 V, <i>f</i> = 100 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	-	6	pF
V <sub>CB</sub> = 20 V, <i>f</i> = 1 MHz					

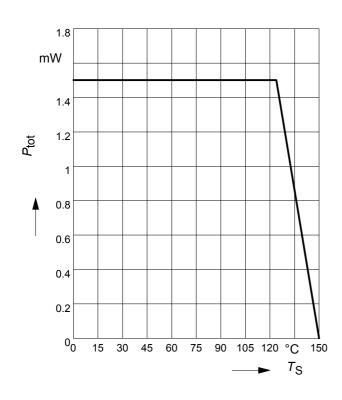


**PZTA92** 

# Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

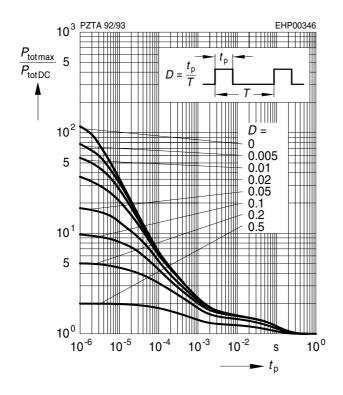
**Transition frequency**  $f_{\rm T} = f(I_{\rm C})$ 

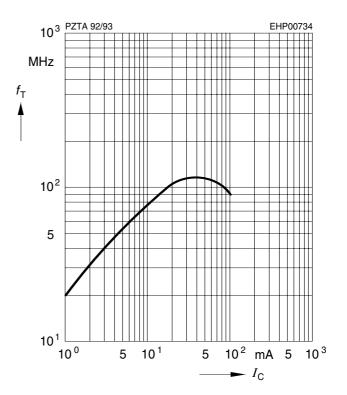
 $V_{CE} = 10V, f = 100MHz$ 



# Permissible pulse load

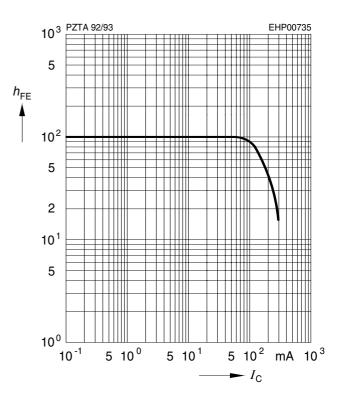
 $P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$ 





# **DC** current gain $h_{\text{FE}} = f(I_{\text{C}})$

 $V_{CE} = 10V$ 

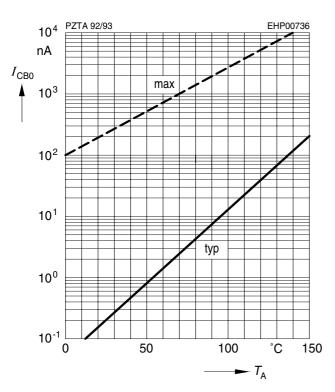




**PZTA92** 

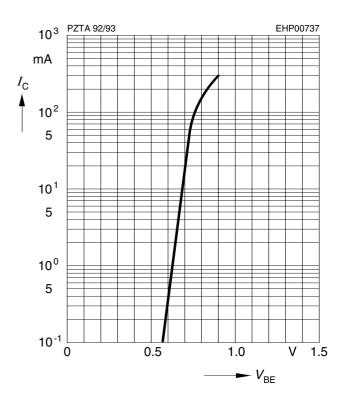
# **Collector cutoff current** $I_{CBO} = f(T_A)$

 $V_{\rm CB}$  = 200V

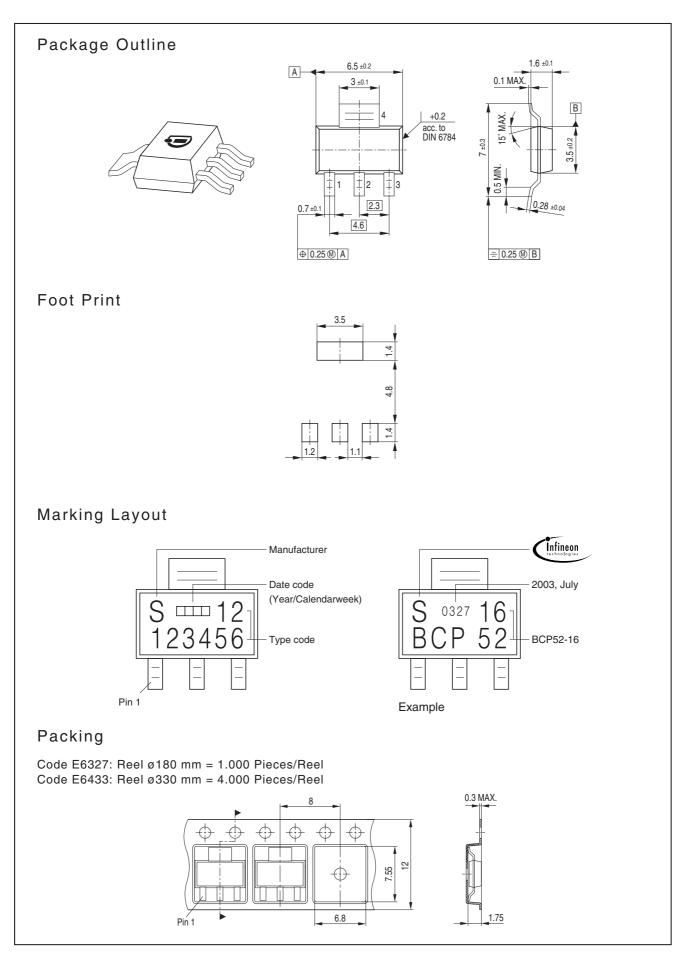


**Collector current**  $I_{\rm C} = f(V_{\rm BE})$ 

*V*<sub>CE</sub> = 10V









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